

2N5302

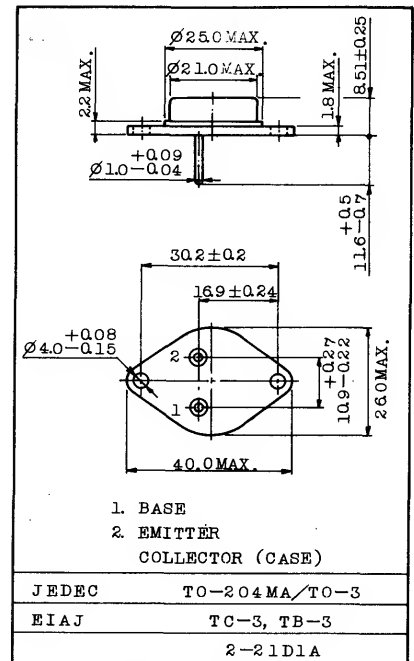
SILICON NPN TRIPLE DIFFUSED TYPE

HIGH POWER SWITCHING, AMPLIFIER, DC-DC CONVERTER,
INVERTER AND REGULATOR APPLICATIONS

FEATURES:

- Specification for h_{FE} and $V_{CE(sat)}$ Up to 30A:
 $h_{FE}=5.0$ (Min.) @ $V_{CE}=4.0V$, $I_C=30A$
 $V_{CE(sat)}=3.0V$ (Max.) @ $I_C=30A$, $I_B=1.0A$
- Low Saturation Voltage:
 $V_{CE(sat)}=0.75V$ (Max.) @ $I_C=10A$, $I_B=1.0A$
 $V_{CE(sat)}=1.7V$ (Max.) @ $I_C=10A$, $I_B=1.0A$
- High Collector Power Dissipation Capability:
 $P_C=200W$ (Max.)
- Complementary to 2N4399

Unit in mm



Weight : 12.6g

MAXIMUM RATINGS ($T_a=25^{\circ}C$)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	60	V
Collector-Emitter Sustaining Voltage		$V_{CEO(SUS)}$	60	V
Emitter-Base Voltage		V_{EBO}	5	V
Collector Current	DC	I_C	30	A
	Peak	I_{CM}	50	A
Base Current		I_B	7.5	A
Collector Power Dissipation ($T_c=25^{\circ}C$)		P_C	200	W
Derate above $25^{\circ}C$			1.14	W/ $^{\circ}C$
Junction Temperature		T_j	200	$^{\circ}C$
Storage Temperature Range		T_{stg}	-65 ~ 200	$^{\circ}C$

※In Accordance with JEDEC Registration Data format JS-6 RDF-2.

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
※ Collector Cut-off Current	I_{CBO}	$V_{CB}=60V, I_E=0$	-	-	1.0	mA
※ Collector Cut-off Current	I_{CEX}	$V_{CE}=60V, V_{BE}=-1.5V$	-	-	1.0	mA
※ Collector Cut-off Current	I_{CEX}	$V_{CE}=60V, V_{BE}=-1.5V, T_c=150^{\circ}C$	-	-	10	mA
※ Collector Cut-off Current	I_{CEO}	$V_{CE}=60V, I_B=0$	-	-	5.0	mA
※ Emitter Cut-off Current	I_{EBO}	$V_{EB}=5V, I_C=0$	-	-	5.0	mA
※ Collector-Emitter Sustaining Voltage	$V_{CEO(SUS)}$	$I_C=200mA, I_B=0$	60	-	-	V
※ DC Current Gain	h_{FE}	$V_{CE}=2.0V, I_C=1.0A$	40	-	-	
		$V_{CE}=2.0V, I_C=15A$	15	-	60	
		$V_{CE}=4.0V, I_C=30A$	5.0	-	-	
※ Base-Emitter Voltage	V_{BE}	$V_{CE}=2.0V, I_C=15A$	-	-	1.7	V
		$V_{CE}=4.0V, I_C=30A$	-	-	3.0	V
※ Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=10A, I_B=1.0A$	-	-	0.75	V
		$I_C=20A, I_B=2.0A$	-	-	2.0	V
		$I_C=30A, I_B=6.0A$	-	-	3.0	V
※ Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=10A, I_B=1.0A$	-	-	1.7	V
		$I_C=15A, I_B=1.5A$	-	-	1.8	V
		$I_C=20A, I_B=2.0A$	-	-	2.5	V
※ Transition Frequency	f_T	$V_{CE}=10V, I_C=1.0A, f=1.0MHz$	2.0	-	-	MHz
※ Small-Signal Current Gain	h_{fe}	$V_{CE}=10V, I_C=1.0A, f=1.0kHz$	40	-	-	
※ Switching Time	Rise Time	t_r	See Fig.1-1	-	1.0	μs
	Storage Time	t_{stg}	See Fig.1-2	-	2.0	μs
	Fall Time	t_f		-	1.0	μs

※ In Accordance with JEDEC Registration Data Format JS-6 RDF-1.

※※ The sustaining voltage $V_{CEO(SUS)}$ MUST NOT be measured on a curve tracer.

Fig. 1 SWITCHING TIME EQUIVALENT TEST CIRCUITS

Fig.1-1 TURN-ON TIME

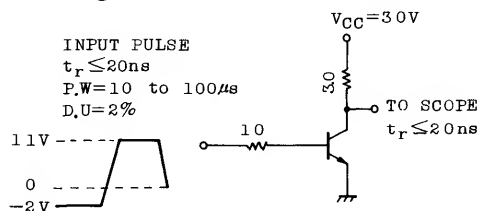


Fig.1-2 TURN-OFF TIME

